Philips Semiconductors

Product specification

Rectifier diodes Schottky barrier

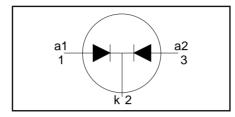
BYV118, BYV118B series

FEATURES

• Low forward volt drop

- Fast switching
- · Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$$V_R = 35 \text{ V}/ 40 \text{ V}/ 45 \text{ V}$$
 $I_{O(AV)} = 10 \text{ A}$
 $V_F \le 0.6 \text{ V}$

GENERAL DESCRIPTION

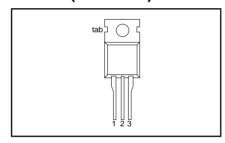
Dual, common cathode schottky rectifier diodes in a conventional leaded plastic package and a surface mounting plastic package. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The BYV118 series is supplied in the SOT78 conventional leaded package. The BYV118B series is supplied in the SOT404 surface mounting package.

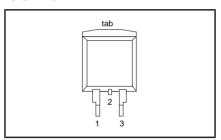
PINNING

PIN	DESCRIPTION		
1	anode 1 (a)		
2	cathode (k) 1		
3	anode 2 (a)		
tab	cathode (k)		

SOT78 (TO220AB)



SOT404



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
		BYV118- BYV118B-		35 35	40 40	45 45	
V_{RRM}	Peak repetitive reverse voltage		-	35	40	45	V
V_{RWM}	Working peak reverse voltage		-	35	40	45	V
V_R	Continuous reverse voltage	T _{mb} ≤ 108 °C	-	35	40	45	V
I _{O(AV)}	Average rectified forward current (both diodes conducting)	square wave; δ = 0.5; $T_{mb} \le$ 127 °C	-		10		А
I _{FRM}	Repetitive peak forward current (per diode)	square wave; $\delta = 0.5$; $T_{mb} \le 127 ^{\circ}C$	-		10		А
I _{FSM}	Non-repetitive peak forward current per diode	t = 10 ms t = 8.3 ms sinusoidal; T_i = 125 °C prior to surge; with reapplied $V_{RRM(max)}$	-		100 110		A A
I _{RRM}	Peak repetitive reverse surge current per diode	pulse width and repetition rate limited by T _{i max}	-		1		Α
T _j	Operating junction temperature	, max	-		150		°C
T_{stg}	Storage temperature		- 65		175		°C

1. It is not possible to make connection to pin 2 of the SOT404 pckage.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-a}	to mounting base	per diode both diodes SOT78 package in free air SOT404 package, pcb mounted, minimum		- - 60 50	4.5 3 - -	K/W K/W K/W K/W
		footprint, FR4 board				

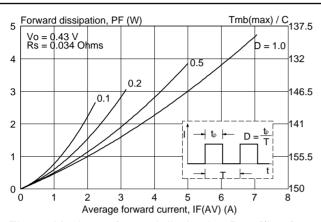
ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified

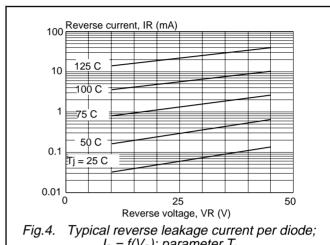
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage per diode	$I_F = 5 A; T_j = 125 ^{\circ}C$	-	0.52	0.6	V
I _R	Reverse current per diode	$I_F = 10 \text{ A}$ $V_R = V_{RWM}$	-	0.72 0.06	0.87 0.5	mA
C _d	Junction capacitance per diode	$V_R = V_{RWM}$; $T_j = 100$ °C $V_R = 5$ V; $f = 1$ MHz, $T_j = 25$ °C to 125°C	- -	6 155	15 -	mA pF

BYV118, BYV118B series

Product specification



Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.



 $I_R = f(V_R)$; parameter T_i

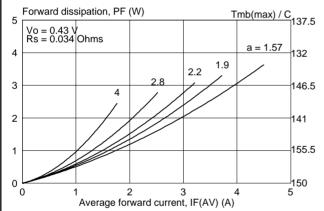


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = form $factor = I_{F(RMS)} / I_{F(AV)}$.

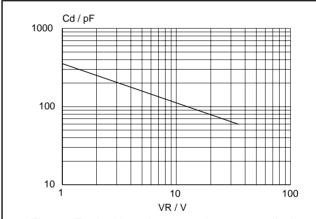


Fig.5. Typical junction capacitance per diode; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25$ °C to 125°C.

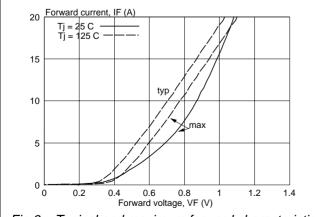


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

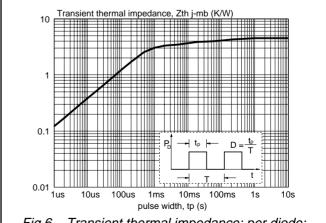
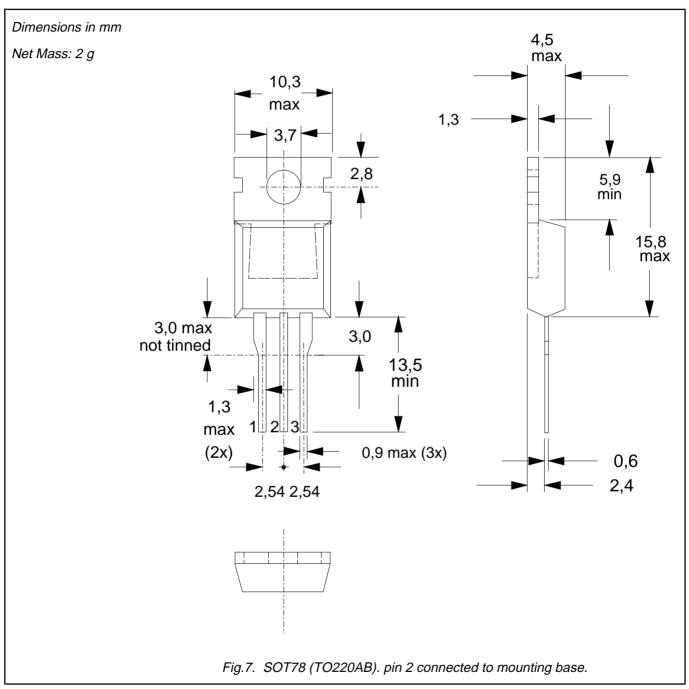


Fig.6. Transient thermal impedance; per diode; $Z_{th\ j-mb} = f(t_p).$

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MECHANICAL DATA

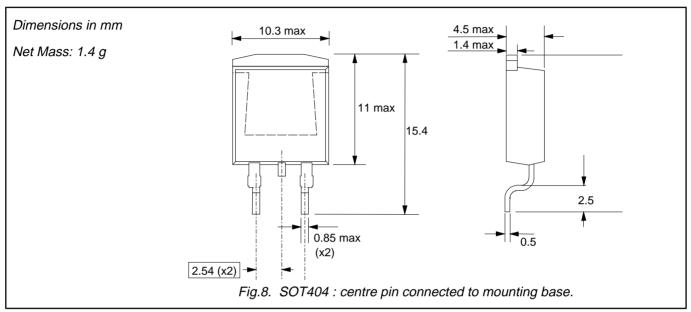


- Notes
 1. Refer to mounting instructions for SOT78 (TO220) envelopes.
 2. Epoxy meets UL94 V0 at 1/8".

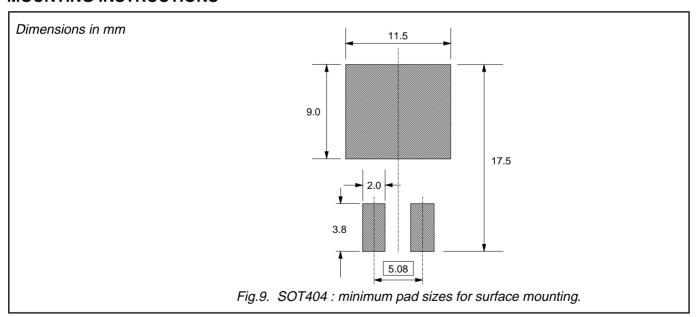
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MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes

1. Plastic meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status					
Objective specification This data sheet contains target or goal specifications for product development.					
Preliminary specification This data sheet contains preliminary data; supplementary data may be published la					
Product specification This data sheet contains final product specifications.					
Limiting values					

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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